

REMARKS

Claims 1 and 3-11 are pending in the instant case.

Claim 2 has been previously cancelled.

Claim 12 (previously Claim 2) has been added herewith.

Claim 4 has been cancelled herewith, without prejudice or disclaimer.

Claim 1 have been amended herewith. Support for this amendment may be found in the specification at least on pages 2-5. Applicants respectfully submit no new matter has been added by way of this amendment.

Claims 1-3 and 5-11 stand rejected under 35 U.S.C. § 102(e) as being anticipated by Zhang *et al.* Applicants respectfully submit the rejection has been rendered moot in light of the instant amendment and request withdrawal of same.

Applicants have amended Claim 1 to provide for an additional irradiation feature, wherein said feature is not provided for by Zhang. All of the elements of Applicants' invention as now claimed are not found in Zhang. Applicants respectfully request withdrawal of the rejection.

Claim 4 stands rejected under 35 U.S.C. § 103(a) as being unpatentable over Zhang as applied to Claim 1 and further in view of JP 08228010A. Applicants respectfully submit the rejection has been rendered moot in light of the instant amendment, wherein Claim 4 has been cancelled, without prejudice or disclaimer. Applicants respectfully request withdrawal of the rejection.

Claim 5 stands rejected under 35 U.S.C. § 103(a) as being unpatentable over Zhang as applied to Claim 1 and further in view of Inou. Applicants respectfully submit the rejection has been rendered moot in light of the instant amendment and request withdrawal of same.

Applicants have amended Claim 1 to provide for an additional irradiation feature, wherein said feature is not provided for by Zhang, nor is said feature found in Inou. A *prima facie* case of obviousness has not been established. Applicants respectfully request withdrawal of the rejection.

CONCLUSION

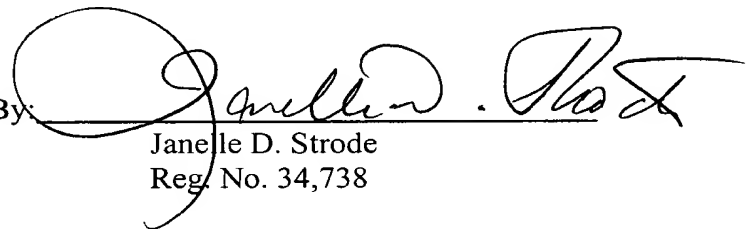
Applicants request prompt and favorable consideration of now pending Claims 1, 3,
and 5-12.

Respectfully submitted,

SONNENSCHN NATH & ROSENTHAL

April 25, 2001

By:

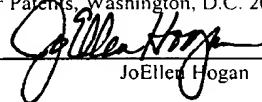

Janele D. Strode
Reg. No. 34,738

SONNENSCHN NATH & ROSENTHAL
P.O. Box #061080
Wacker Drive Station
Sears Tower
Chicago, IL 60606-6404
(312)876-8000

I hereby certify that this document and any being referred to as
attached or enclosed is being deposited with the United States
Postal Service as first class mail in an envelope addressed to
Assistant Commissioner for Patents, Washington, D.C. 20231, on

4/25/01

Date


JoEllen Hogan

RECEIVED

MAY 01 2001

OFFICE OF PETITIONS

APPENDIX

1. (Twice Amended) A semiconductor device manufacturing method comprising
[the steps of]:

forming a semiconductor film on a substrate;

forming a hydrogen-containing film on said semiconductor film

[calculating pulse energy beam values for an energy density, a number of pulses, and
a pulse width of a pulse energy beam so that said pulse energy beam does not melt said
semiconductor film;] and

irradiating [said] pulse energy beam [using said calculated values] to heat said
hydrogen-containing film and thereby diffuse hydrogen in said hydrogen-containing film into
said semiconductor layer;

further comprising irradiating other pulse energy beam to crystallize or re-crystallize
said semiconductor film after the step of forming said semiconductor film on said substrate
and before the step of forming said hydrogen-containing film on said semiconductor film,
energy density of said pulse energy beam used for heating said hydrogen-containing film
being set lower than energy density of said other pulse energy beam being used to crystallize
or re-crystallize said semiconductor film.

Please add New Claim 12:

12. The semiconductor device manufacturing method of Claim 1 wherein energy density, number of pulses and pulse width of said pulse energy beam are determined not to melt said semiconductor film.